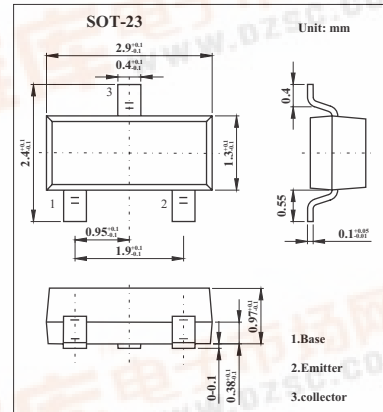


SMD Type Transistors

Silicon PNP Epitaxial
2SA1484

■ Features



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V _{CB0}	-90	V
Collector to emitter voltage	V _{CEO}	-90	V
Emitter to base voltage	V _{EBO}	-5	V
Collector current	I _C	-100	mA
Collector power dissipation	P _C	150	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = -10 μA, I _E = 0	-90			V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = -1 mA, R _{BE} = ∞	-90			V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -10 μA, I _C = 0	-5			V
Collector cutoff current	I _{CBO}	V _{CB} = -70 V, I _E = 0			-0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} = -2 V, I _C = 0			-0.1	μA
DC current transfer ratio	h _{FE}	V _{CE} = -12 V, I _C = -2 mA (*)	250		800	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -10 mA, I _B = -1 mA (*)			-0.15	V
Base to emitter saturation voltage	V _{BE(sat)}	I _C = -10 mA, I _B = -1 mA (*)			-1	V

* Pulse test.

■ hFE Classification

Marking	IRD	IRE
hFE	250~500	400~800

